## NLAS4685

## Ultra-Low Resistance Dual SPDT Analog Switch

The NLAS4685 is an advanced CMOS analog switch fabricated in Sub-micron silicon gate CMOS technology. The device is a dual Independent Single Pole Double Throw (SPDT) switch featuring Ultra-Low $\mathrm{R}_{\mathrm{ON}}$ of $0.8 \Omega$, for the Normally Closed (NC) switch and for the Normally Opened switch (NO) at 2.7 V .

The part also features guaranteed Break Before Make switching, assuring the switches never short the driver.

The NLAS 4685 is available in a $2.0 \times 1.5 \mathrm{~mm}$ bumped die array, with a $3 \times 4$ arrangement of solder bumps. The pitch of the solder bumps is 0.5 mm for easy handling.

## Features

- Ultra-Low $\mathrm{R}_{\mathrm{ON}},<0.8 \Omega$ at 2.7 V
- Threshold Adjusted to Function with 1.8 V Control at $\mathrm{V}_{\mathrm{CC}}=2.7-3.3 \mathrm{~V}$
- Single Supply Operation from 1.8-5.5 V
- Tiny $2 \times 1.5 \mathrm{~mm}$ Bumped Die
- Low Crosstalk, $<81 \mathrm{~dB}$ at 100 kHz
- Full $0-\mathrm{V}_{\mathrm{CC}}$ Signal Handling Capability
- High Isolation, -65 dB at 100 kHz
- Low Standby Current, < 50 nA
- Low Distortion, < 0.14\% THD
- $\mathrm{R}_{\mathrm{ON}}$ Flatness of $0.15 \Omega$
- Pin for Pin Replacement for MAX4685
- $\mathrm{Pb}-$ Free Package is Available


## Applications

- Cell Phone
- Speaker Switching
- Power Switching (Up to 100 mA )
- Modems
- Automotive

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PIN CONNECTIONS AND LOGIC DIAGRAM


## FUNCTION TABLE

| IN 1, $\mathbf{2}$ | NO 1, $\mathbf{2}$ | NC 1, $\mathbf{2}$ |
| :---: | :---: | :---: |
| 0 | OFF | ON |
| 1 | ON | OFF |

ORDERING INFORMATION

| Device | Package | Shipping ${ }^{\dagger}$ |
| :--- | :---: | :---: |
| NLAS4685FCT1 | Microbump | 3000 Tape/Reel |
| NLAS4685FCT1G | Microbump <br> (Pb-Free) | 3000 Tape/Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NLAS4685

MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
| :--- | :--- | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | Positive DC Supply Voltage | -0.5 to +7.0 | V |
| $\mathrm{~V}_{\mathrm{IS}}$ | Analog Input Voltage $\left(\mathrm{V}_{\mathrm{NO}}, \mathrm{V}_{\mathrm{NC}}\right.$, or $\left.\mathrm{V}_{\mathrm{COM}}\right)($ (Note 1) | $-0.5 \leq \mathrm{V}_{\mathrm{IS}} \leq \mathrm{V}_{\mathrm{CC}}+0.5$ | V |
| $\mathrm{~V}_{\mathrm{IN}}$ | Digital Select Input Voltage | $-0.5 \leq \mathrm{V}_{\mathrm{I}} \leq+7.0$ | V |
| $\mathrm{I}_{\mathrm{IK}}$ | DC Current, Into or Out of Any Pin | $\pm 50$ | mA |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Signal voltage on NC, NO, and COM exceeding VCC or GND are clamped by the internal diodes. Limit forward diode current to maximum current rating.

## RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
| :--- | :--- | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | DC Supply Voltage | 1.8 | 5.5 | V |
| $\mathrm{~V}_{\mathrm{IN}}$ | Digital Select Input Voltage | GND | 5.5 | V |
| $\mathrm{~V}_{\mathrm{IS}}$ | Analog Input Voltage (NC, NO, COM) | GND | $\mathrm{V}_{\mathrm{CC}}$ | V |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature Range | -55 | +125 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{t}_{\mathrm{r}}, \mathrm{t}_{\mathrm{f}}$ | Input Rise or Fall Time, SELECT |  | $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V} \pm 0.3 \mathrm{~V}$ | 0 |
|  |  | $\mathrm{~V}_{\mathrm{CC}}=5.0 \mathrm{~V} \pm 0.5 \mathrm{~V}$ | 0 | 100 |

DC CHARACTERISTICS - Digital Section (Voltages Referenced to GND)

| Symbol | Parameter | Condition | $\mathrm{V}_{\mathrm{cc}} \pm 10 \%$ | Guaranteed Limit |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | $-55^{\circ} \mathrm{C}$ to $25^{\circ} \mathrm{C}$ | $<85^{\circ} \mathrm{C}$ | $<125^{\circ} \mathrm{C}$ |  |
| $\mathrm{V}_{\mathrm{IH}}$ | Minimum High-Level Input Voltage, Select Inputs |  | 2.0 | 1.4 | 1.4 | 1.4 | V |
|  |  |  | 2.5 | 1.4 | 1.4 | 1.4 |  |
|  |  |  | 3.0 | 1.4 | 1.4 | 1.4 |  |
|  |  |  | 5.0 | 2.0 | 2.0 | 2.0 |  |
| $\mathrm{V}_{\text {IL }}$ | Maximum Low-Level Input Voltage, Select Inputs |  | 2.0 | 0.5 | 0.5 | 0.5 | V |
|  |  |  | 2.5 | 0.5 | 0.5 | 0.5 |  |
|  |  |  | 3.0 | 0.5 | 0.5 | 0.5 |  |
|  |  |  | 5.0 | 0.8 | 0.8 | 0.8 |  |
| $\mathrm{I}_{\mathrm{IN}}$ | Maximum Input Leakage Current, Select Inputs | $\mathrm{V}_{\mathrm{IN}}=5.5 \mathrm{~V}$ or GND | 5.5 | $\pm 1.0$ | $\pm 1.0$ | $\pm 1.0$ | $\mu \mathrm{A}$ |
| IOFF | Power Off Leakage Current | $\mathrm{V}_{\mathrm{IN}}=5.5 \mathrm{~V}$ or GND | 0 | $\pm 10$ | $\pm 10$ | $\pm 10$ | $\mu \mathrm{A}$ |
| ICC | Maximum Quiescent Supply Current | Select and $\mathrm{V}_{\text {IS }}=\mathrm{V}_{\mathrm{CC}}$ or GND | 5.5 | $\pm 180$ | $\pm 200$ | $\pm 200$ | nA |

DC ELECTRICAL CHARACTERISTICS - Analog Section

| Symbol | Parameter | Condition | $\mathrm{V}_{\mathrm{cc}} \pm 10 \%$ | Guaranteed Maximum Limit |  |  |  |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | $-55^{\circ} \mathrm{C}$ to $25^{\circ} \mathrm{C}$ |  | $<85^{\circ} \mathrm{C}$ |  | $<125^{\circ} \mathrm{C}$ |  |  |
|  |  |  |  | Min | Max | Min | Max | Min | Max |  |
| $\begin{aligned} & \hline \mathrm{R}_{\mathrm{ON}} \\ & \text { (NC, NO) } \end{aligned}$ | "ON" Resistance (Note 2) | $\begin{aligned} & \mathrm{V}_{I N} \geq \mathrm{V}_{\mathrm{IH}} \\ & \mathrm{~V}_{\mathrm{IS}}=\mathrm{GND} \text { to } \mathrm{V}_{\mathrm{CC}} \\ & \mathrm{I}_{\mathrm{IN}} \leq 100 \mathrm{~mA} \end{aligned}$ | $\begin{aligned} & 2.5 \\ & 3.0 \\ & 5.0 \end{aligned}$ |  | $\begin{aligned} & 2.0 \\ & 0.8 \\ & 0.8 \end{aligned}$ |  | $\begin{aligned} & 2.0 \\ & 0.8 \\ & 0.8 \end{aligned}$ |  | $\begin{aligned} & \hline 2.0 \\ & 1.0 \\ & 0.9 \end{aligned}$ | $\Omega$ |
| RFLAT (NC, NO) | On-Resistance Flatness (Notes 2, 4) | $\begin{aligned} & \mathrm{I}_{\mathrm{COM}}=100 \mathrm{~mA} \\ & \mathrm{~V}_{\text {IS }}=0 \text { to } \mathrm{V}_{\mathrm{CC}} \end{aligned}$ | $\begin{aligned} & 2.5 \\ & 3.0 \\ & 5.0 \end{aligned}$ |  | $\begin{aligned} & 0.35 \\ & 0.35 \\ & 0.35 \end{aligned}$ |  | $\begin{aligned} & 0.35 \\ & 0.35 \\ & 0.35 \end{aligned}$ |  | $\begin{aligned} & 0.35 \\ & 0.35 \\ & 0.35 \end{aligned}$ | $\Omega$ |
| $\Delta \mathrm{R}_{\text {ON }}$ | On-Resistance Match Between Channels (Notes 2 and 3) | $\begin{aligned} & \mathrm{V}_{\text {IS }}=1.3 \mathrm{~V} ; \\ & \mathrm{I}_{\text {COM }}=100 \mathrm{~mA} \\ & \mathrm{~V}_{\text {IS }}=1.5 \mathrm{~V} ; \\ & \text { I COM }^{2} 100 \mathrm{~mA} \\ & \mathrm{~V}_{\text {IS }}=2.8 \mathrm{~V} ; \\ & \text { ICOM }^{\text {C }} 000 \mathrm{~mA} \end{aligned}$ | $\begin{aligned} & 2.5 \\ & 3.0 \\ & 5.0 \end{aligned}$ |  | $\begin{aligned} & 0.18 \\ & 0.06 \\ & 0.06 \end{aligned}$ |  | $\begin{aligned} & \hline 0.18 \\ & 0.06 \\ & 0.06 \end{aligned}$ |  | $\begin{aligned} & 0.18 \\ & 0.06 \\ & 0.06 \end{aligned}$ | $\Omega$ |
| $\mathrm{I}_{\text {NC(OFF) }}$ ${ }^{\mathrm{NO} O(O F F)}$ | NC or NO Off Leakage Current (Figure 10) | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IL}} \text { or } \mathrm{V}_{\mathrm{IH}} \\ & \mathrm{~V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=1.0 \\ & \mathrm{~V}_{\mathrm{COM}}=4.5 \mathrm{~V} \end{aligned}$ | 5.5 | -1 | 1 | -10 | 10 | -150 | 150 | nA |
| $\mathrm{I}_{\text {COM (ON) }}$ | COM ON Leakage Current (Figure 10) | $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IL}} \text { or } \mathrm{V}_{\mathrm{IH}}$ <br> $\mathrm{V}_{\mathrm{NO}} 1.0 \mathrm{~V}$ or 4.5 V with <br> $\mathrm{V}_{\mathrm{NC}}$ floating or <br> $\mathrm{V}_{\mathrm{NC}} 1.0 \mathrm{~V}$ or 4.5 V with <br> $\mathrm{V}_{\mathrm{NO}}$ floating <br> $\mathrm{V}_{\mathrm{COM}}=1.0 \mathrm{~V}$ or 4.5 V | 5.5 | -1 | 1 | -10 | 10 | -150 | 150 | nA |

2. Guaranteed by design. Resistance measurements do not include test circuit or package resistance.
3. $\Delta R_{O N}=R_{O N(M A X)}-R_{O N(M I N)}$ between all switches.
4. Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges.

AC ELECTRICAL CHARACTERISTICS (Input $\mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=3.0 \mathrm{~ns}$ )

| Symbol | Parameter | Test Conditions | $\begin{aligned} & \mathrm{V}_{\mathrm{cc}} \\ & (\mathrm{~V}) \end{aligned}$ | $\begin{aligned} & V_{\text {IS }} \\ & \text { (V) } \end{aligned}$ | Guaranteed Maximum Limit |  |  |  |  |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  | $-55^{\circ} \mathrm{C}$ to $25^{\circ} \mathrm{C}$ |  |  | $<85^{\circ} \mathrm{C}$ |  | $<125^{\circ} \mathrm{C}$ |  |  |
|  |  |  |  |  | Min | Typ* | Max | Min | Max | Min | Max |  |
| ton | Turn-On Time | $R_{L}=50 \Omega, C_{L}=35 \mathrm{pF}$ <br> (Figures 2 and 3 ) | $\begin{aligned} & 2.5 \\ & 3.0 \\ & 5.0 \end{aligned}$ | $\begin{aligned} & 1.3 \\ & 1.5 \\ & 2.8 \end{aligned}$ |  |  | 55 50 30 |  | 65 60 35 |  | 70 60 35 | ns |
| toff | Turn-Off Time | $\mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF}$ <br> (Figures 2 and 3 ) | $\begin{aligned} & 2.5 \\ & 3.0 \\ & 5.0 \end{aligned}$ | $\begin{aligned} & 1.3 \\ & 1.5 \\ & 2.8 \end{aligned}$ |  |  | 55 50 25 |  | 65 60 30 |  | $\begin{aligned} & 70 \\ & 60 \\ & 30 \end{aligned}$ | ns |
| $\mathrm{t}_{\text {BBM }}$ | Minimum Break-Before-Make Time | $\begin{aligned} & \mathrm{V}_{\mathrm{IS}}=3.0 \\ & \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} \\ & \text { (Figure 1) } \end{aligned}$ | 3.0 | 1.5 | 2 | 15 |  |  |  |  |  | ns |


|  |  | Typical @ 25, $\mathbf{V}_{\text {CC }}=\mathbf{5 . 0} \mathbf{V}$ | $\mathbf{V}_{\text {CC }}=\mathbf{3 . 0} \mathbf{V}$ |  |
| :--- | :--- | :---: | :---: | :---: |
| $\mathrm{C}_{\text {NC }}$ Off | NC Off Capacitance, $\mathrm{f}=1 \mathrm{MHz}$ |  | 208 |  |
| $\mathrm{C}_{\text {NO }}$ Off | NO Off Capacitance, $\mathrm{f}=1 \mathrm{MHz}$ |  | 102 |  |
| $\mathrm{C}_{\text {NC }}$ On | NC On Capacitance, $\mathrm{f}=1 \mathrm{MHz}$ |  | 547 | pF |
| $\mathrm{C}_{\text {NO }}$ On | NO On Capacitance, $\mathrm{f}=1 \mathrm{MHz}$ |  | 431 |  |

${ }^{*}$ Typical Characteristics are at $25^{\circ} \mathrm{C}$.

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted) (Note 6)

| Symbol | Parameter | Condition | $\stackrel{\mathrm{v}_{\mathrm{cc}}}{\mathrm{~V}}$ | Typical | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | $25^{\circ} \mathrm{C}$ |  |
| BW | Maximum On-Channel -3dB Bandwidth or Minimum Frequency Response | $\mathrm{V}_{\mathrm{IN}}=0 \mathrm{dBm}$ <br> $\mathrm{V}_{\text {IN }}$ centered between $\mathrm{V}_{\mathrm{CC}}$ and GND <br> (Figure 4) | 3.0 | 11.5 | MHz |
| $\mathrm{V}_{\text {ONL }}$ | Maximum Feed-through On Loss | $\mathrm{V}_{\mathrm{IN}}=0 \mathrm{dBm} @ 100 \mathrm{kHz}$ to 50 MHz <br> $\mathrm{V}_{\text {IN }}$ centered between $\mathrm{V}_{\mathrm{CC}}$ and GND (Figure 4) | 3.0 | -0.05 | dB |
| VISO | Off-Channel Isolation | $\begin{aligned} & \mathrm{f}=100 \mathrm{kHz} ; \mathrm{V}_{\mathrm{IS}}=1 \mathrm{VRMS} ; \mathrm{C}_{\mathrm{L}}=5 \mathrm{nF} \\ & \mathrm{~V}_{\mathrm{IN}} \text { centered between } \mathrm{V}_{\mathrm{CC}} \text { and } \operatorname{GND} \text { (Figure 4) } \end{aligned}$ | 3.0 | -65 | dB |
| Q | Charge Injection Select Input to Common I/O | $\begin{aligned} & V_{I N}=V_{C C \text { to }} G N D, R_{I S}=0 \Omega, C_{L}=1 \mathrm{nF} \\ & Q=C_{L}-\Delta V_{\text {OUT }} \text { (Figure 5) } \end{aligned}$ | $\begin{aligned} & 3.0 \\ & 5.0 \end{aligned}$ | $\begin{aligned} & 15 \\ & 20 \end{aligned}$ | pC |
| THD | Total Harmonic Distortion THD + Noise | $\begin{aligned} & \mathrm{F}_{\text {IS }}=20 \mathrm{~Hz} \text { to } 20 \mathrm{kHz}, \mathrm{R}_{\mathrm{L}}=\mathrm{R}_{\text {gen }}=600 \Omega, \mathrm{C}_{\mathrm{L}}=50 \mathrm{pF} \\ & \mathrm{~V}_{\text {IS }}=1 \mathrm{VMS} \end{aligned}$ | 3.0 | 0.14 | \% |
| VCT | Channel-to-Channel Crosstalk | $\mathrm{f}=100 \mathrm{kHz} ; \mathrm{V}_{\mathrm{IS}}=1 \mathrm{VRMS}, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{R}_{\mathrm{L}}=50 \Omega$ <br> $\mathrm{V}_{\text {IN }}$ centered between $\mathrm{V}_{\mathrm{CC}}$ and GND (Figure 4) | 3.0 | -81 | dB |

5. Off-Channel Isolation $=20 \log 10(\mathrm{Vcom} / \mathrm{Vno}), \mathrm{Vcom}=$ output, $\mathrm{Vno}=$ input to off switch.
6. $-40^{\circ} \mathrm{C}$ specifications are guaranteed by design.


Figure 1. $\mathrm{t}_{\mathrm{BBM}}$ (Time Break-Before-Make)


Figure 2. $\mathrm{t}_{\mathrm{ON}} / \mathrm{t}_{\mathrm{OFF}}$


Figure 3. $\mathrm{t}_{\mathrm{ON}} / \mathrm{t}_{\mathrm{OFF}}$


Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. $\mathrm{V}_{\text {ISO }}$, Bandwidth and $\mathrm{V}_{\text {ONL }}$ are independent of the input signal direction.
$\mathrm{V}_{\text {ISO }}=$ Off Channel Isolation $=20 \log \left(\frac{\mathrm{~V}_{\text {OUT }}}{\mathrm{V}_{\text {IN }}}\right)$ for $\mathrm{V}_{\text {IN }}$ at 100 kHz
$\mathrm{V}_{\text {ONL }}=$ On Channel Loss $=20 \log \left(\frac{\mathrm{~V}_{\mathrm{OUT}}}{\mathrm{V}_{\mathrm{IN}}}\right)$ for $\mathrm{V}_{\mathrm{IN}}$ at 100 kHz to 50 MHz
Bandwidth $(\mathrm{BW})=$ the frequency 3 dB below $\mathrm{V}_{\mathrm{ONL}}$
$\mathrm{V}_{\mathrm{CT}}=$ Use $\mathrm{V}_{\text {ISO }}$ setup and test to all other switch analog input/outputs terminated with $50 \Omega$

Figure 4. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V ${ }_{\text {ONL }}$


Figure 5. Charge Injection: (Q)


Figure 6. Total Harmonic Distortion Plus Noise versus Frequency


Figure 7. Voltage in Threshold on Logic Pins


Figure 9. T-on/T-off Time versus Temperature


Figure 8. Charge Injection versus $\mathrm{V}_{\text {is }}$


Figure 10. NO/NC Current Leakage Off and On,

$$
\mathrm{V}_{\mathrm{cc}}=5 \mathrm{~V}
$$



Figure 11. I Ic Current Leakage versus Temperature $\mathrm{V}_{\mathrm{CC}}=5.5 \mathrm{~V}$


Figure 12. NC/NO On-Resistance versus COM Voltage


Figure 13. NC/NO On-Resistance versus COM Voltage


Figure 14. NC/NO Bandwidth and Phase Shift versus Frequency


Figure 15. NC/NO Off Isolation and Crosstalk


Figure 16. T-on/T-off versus $\mathrm{V}_{\mathrm{CC}}$


Figure 17. NC/NO On-Resistance versus COM Voltage


Figure 18. NC/NO On-Resistance versus COM Voltage


## 10 PIN FLIP-CHIP

CASE 489AA-01
ISSUE A
DATE 04 MAY 2004

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLING DIMENSION: MILLIMETERS.
3. COPLANARITY APPLIES TO SPHERICAL CROWNS OF SOLDER BALLS.

|  | MILLIMETERS |  |
| :---: | :---: | :---: |
| DIM | MIN | MAX |
| A | --- | 0.650 |
| A1 | 0.210 | 0.270 |
| A2 | 0.280 | 0.380 |
| D | 1.965 BSC |  |
| E | 1.465 BSC |  |
| b | 0.250 | 0.350 |
| e | 0.500 BSC |  |
| D1 | 1.500 BSC |  |
| E1 | 1.000 BSC |  |

GENERIC
MARKING DIAGRAM*

xxxx = Specific Device Code
YY = Year
WW = Work Week
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " r ", may or may not be present.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | 10 PIN FLIP-CHIP | PAGE 1 OF 1 |

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